Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

Claim 1 (currently amended): A semiconductor module, comprising:

a substrate body having an insulating ceramic layer with a top side, and a metal layer fixedly joined to said top side of said insulating ceramic layer, said substrate body being one of a direct copper bonded (DCB) substrate and an active metallic brazed (AMB) substrate;

at least one connection conductor laser-welded to said metal layer, said connection conductor having a foot being bent at right angles, said foot having at least one slot formed therein; and

at least one semiconductor component disposed directly on said substrate body facing said metal layer.

Claim 2 (original): The semiconductor module according to claim 1, wherein said insulating ceramic layer of said substrate body is formed of Al_2O_3.

Claim 3 (original): The semiconductor module according to claim 1, wherein said metal layer is formed of at least one material selected from the group consisting of copper and aluminium.

Claim 4 (cancelled).

Claim 5 (original): The semiconductor module according to claim 1, wherein said insulating ceramic layer contains AlN.

Claim 6 (original): The semiconductor module according to claim 1, wherein said insulating ceramic layer contains BeO.

Claim 7 (original): The semiconductor module according to claim 1, wherein said connection conductor is one of a plurality of connection conductors each formed of a at least one material selected from the group consisting of Cu, Al, CuSn and CnZn.

Claim 8 (original): The semiconductor module according to claim 1, including a coating disposed on said metal layer.

Claims 9-10 (cancelled).

Claim 11 (original): The semiconductor module according to claim 10, wherein said slot has a given width that is approximately equal to a thickness of said foot.

Claim 12 (withdrawn): A method for fabricating a semiconductor module, which comprises the steps of:

providing a substrate body having an insulating ceramic layer and a metal layer disposed on and fixedly joined to a top side of the insulating ceramic layer;

disposing at least one semiconductor component directly on the substrate body facing the metal layer; and

joining at least one connection conductor to the metal layer by a welding process.

Claim 13 (withdrawn): The method according to claim 12, which comprises joining the connection conductor to the metal layer by forming successive spot welds.